



Attorney Docket No.: SSI-00501

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
Maximilian A. Biberger et al.
Serial No.: 09/912,844
Filed: July 24, 2001

HIGH PRESSURE PROCESSING For:

CHAMBER FOR

SEMICONDUCTOR SUBSTRATE

(408) 530-9700 Customer No.: 28960

162 N. Wolfe Road Sunnyvale, CA 94086

Group Art Unit: 1763

Examiner: Ram N. Kackar

TRANSMITTAL LETTER

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313

Sir:

Enclosed please find a Supplemental Information Disclosure Statement and Form PTO-1449, including copies of the references contained thereon, for filing in the U.S. Patent and Trademark Office.

You will also find enclosed the associated Transmittals, Electronic Information Disclosure Statements, and United States Patent and Trademark Office Acknowledgment Receipts for the electronically filed Information Disclosure Statement (EFS ID #49914); (EFS ID #49915); (EFS ID#49916); and (EFS ID#49917) filed on October 29, 2003.

The Commissioner is hereby authorized to charge any additional fee or credit overpayment to our Deposit Account No. <u>08-1275</u>. An originally executed duplicate of this transmittal is enclosed for this purpose.

Respectfully submitted,

HAVERSTOCK & OWENS LLP

Thomas B. Haverstock

Reg. No.: 32,571

Attorneys for Applicants

CERTIFICATE OF MAILING (C7 CFR 9 1.8(2)) I hereby confly that fair appet (along with any actioned to as inding the hold on recional) is being the problem to be solved in without any the dollar characters with the U.S. For all 3 without the dollar characters are as first classically in an envelopment to the conflict classical in an envelopment of the south to the command of the formation of the formation of the problem. P.C. Box 1450 Maxandria, 1/0 2231(3-10.1)

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Attorney Docket No.: SSI-00501

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In re Application of:

Maximilian A. Biberger et al.

Serial No.: 09/912,844

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Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313 Group Art Unit: 1763

Examiner: Ram N. Kackar

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

162 N. Wolfe Road Sunnyvale, CA 94086 (408) 530-9700

Sir:

The citations listed below, copies attached, may be material to the examination of the above-identified application, and are therefore submitted in compliance with the duty of disclosure defined in 37 C.F.R. §§ 1.56 and 1.97. The Examiner is requested to make these citations of official record in this application.

United States Patents or Published Patent Applications have been filed electronically (EFS ID #49914); (EFS ID #49915); (EFS ID#49916); and (EFS ID#49917). Applicants have become aware of the following printed publication which may be material to the examination of this application:

- Chinese Publication No. CN 1399790 A;
- German Publication No. DE 36 08 783 A1;
- German Publication No. DE 198 60 084 A1;
- European Publication No. EP 0 244 951 A2;
- European Publication No. EP 0 272 141 A2;
- European Publication No. EP 0 453 867 A1;
- European Publication No. EP 0 572 913 A1;
- European Publication No. EP 0 587 168 A1;
- European Publication No. EP 0 679 753 B1;
 European Publication No. EP 0 903 775 A2;

Attorney Docket No.: <u>SSI-00501</u>

- French Publication No. FR 1 499 491;
- Great Britain Publication No. GB 2 003 975;
- Great Britain Publication No. GB 2 193 482;
- Japanese Patent Abstract JP 2-148841;
- Japanese Patent Abstract JP 2-209729;
- Japanese Patent Abstract JP 11-200035;
- Japanese Patent Abstract JP 56-142629;
- Japanese Patent Abstract JP 60-238479;
- Japanese Patent Abstract JP 60-246635;
- Japanese Patent Abstract JP 61-231166;
- Japanese Patent Abstract JP 62-125619;
- Japanese Patent Abstract JP 63-303059;
- Swiss Publication No. SE 251213;
- PCT Publication No. WO 87/07309;
- PCT Publication No. WO 00/36635;
- PCT Publication No. WO 01/55628 A1;
- PCT Publication No. WO 01/68279 A2;
- PCT Publication No. WO 01/74538 A1;
- PCT Publication No. WO 01/85391 A2;
- PCT Publication No. WO 01/94782 A3;
- PCT Publication No. WO 02/16051 A2;
- PCT Publication No. WO 03/030219 A2;
- Hideaki Itakura et al., "Multi-Chamber Dry Etching System", Solid State Technology, April 1982, pp. 209-214;
- Sun, Y.P. et al., "Preparation of Polymer-Protected Semiconductor Nanoparticles Through the Rapid Expansion of Supercritical Fluid Solution," Chemical Physics Letters, pp. 585-588, May 22, 1998;
- Dahmen, N. et al., "Supercritical Fluid Extraction of Grinding and Metal Cutting Waste Contaminated with Oils," Supercritical Fluids - Extraction and Pollution Prevention, ACS Symposium Series, Vol. 670, pp. 270-279, 21 Oct 1997;
- Xu, C. et al., "Submicron-Sized Spherical Yttrium Oxide Based Phosphors Prepared by Supercritical CO2-Assisted aerosolization and pyrolysis," Appl. Phys. Lett., Vol. 71, No.12, September 22, 1997, pp. 1643-1645;

PATENT Attorney Docket No.: SSI-00501

Courtecuisse, V.G. et al., "Kinetics of the Titanium Isopropoxide Decomposition in Supercritical Isopropyl Alcohol, "Ind. Eng. Chem. Res., Vol. 35, No. 8, pp. 2539-2545, Aug 1996;

- Gallagher-Wetmore, P. et al., "Supercritical Fluid Processing: A New Dry Technique for Photoresist Developing," SPIE Vol. 2438, pp.694-708, Jun. 1995.
- Purtell, R, et al., "Precision Parts Cleaning using Supercritical Fluids," J. Vac, Sci, Technol. A. Vol. 11, No. 4, July 1993, pp. 1696-1701;
- Matson, D.W. et al., "Rapid Expansion of Supercritical Fluid Solutions: Solute Formation of Powders, Thin Films, and Fibers," Ind. Eng. Chem. Res., Vol. 26, No. 11, pp. 2298-2306, 1987;
- Tolley, W.K. et al., "Stripping Organics from Metal and Mineral Surfaces using Supercritical Fluids," Separation Science and Technology, Vol. 22, pp. 1087-1101, 1987;
- Joseph L. Foszcz, "Diaphragm Pumps Eliminate Seal Problems", Plant Engineering, pp. 1-5, February 1, 1996; and
- Bob Agnew, "WILDEN Air-Operated Diaphragm Pumps", Process & Industrial Training Technologies, Inc., 1996.

This Supplemental Information Disclosure Statement under 37 C.F.R. §§ 1.56 and 1.97 is not to be construed as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that anyone or more of these citations constitutes prior art.

> Respectfully submitted, HAVERSTOCK & OWENS LLP

10-29-03

Reg. No.: 32,571

Attorneys for Applicants

CERTIFICATE OF MAILING (27 CFR § 1.8(a))

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FORM PTO-1449 (Modified)

(37 CFR § 1.98(b))

OCT 3 1 2003

U.S. Department of Commerce Patent and Trademark Office

Attorney Docket No.: SSI-00501

Applicants: Maximilian A. Biberger et al.

Serial No.: 09/912,844

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use Several Short of Necessary)

Filing Date: July 24, 2001

Group Art Unit: 1763

FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS

		Document				C. 3: -1	Translation	
		Document Number	Publication Date	Country / Patent Office	Class	Subclass	Yes	No
	AA	CN 1399790 A	02/26/03	China	H01L	21/00		х
:	AB	DE 36 08 783 A1	09/17/87	Germany	C30B	25/12		X
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	BE	WO 02/16051 A2	02/28/02	PCT	B05D			,
	BF	WO 03/030219 A2	10/04/03	PCT	HOIL			>
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EXAMINER:

Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449 (Modified)

U.S. Department of Commerce Patent and Trademark Office Attorney Docket No.: SSI-00501

Serial No.: 09/912,844

EXE STATEMENT BY APPLICANT ON DISCLOSIFICE STATEMENT Applicants: Maximilian A. Biberger et al. Filing Date: July 24, 2001 Group Art Unit: 1763 (37 CFR & 1 98(b)) FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS Translation Document Number Publication Date Country / Patent Office Class Subclass Yes No ΒJ BK BL BM BN BO OTHER DOCUMENTS (Including Author, Title, Date, Relevant Pages, Place of Publication) BP Hideaki Itakura et al., "Multi-Chamber Dry Etching System", Solid State Technology, April 1982, pp. 209-214. Sun, Y.P. et al., "Preparation of Polymer-Protected Semiconductor Nanoparticles Through the Rapid Expansion of Supercritical Fluid Solution," Chemical Physics Letters, pp. 585-588, May 22, 1998. BQ Dahmen, N. et al., "Supercritical Fluid Extraction of Grinding and Metal Cutting Waste Contaminated with Oils," Supercritical Fluids - Extraction and Pollution Prevention, ACS Symposium Series, Vol. 670, pp. 270-279, 21 Oct 1997. BR Xu, C. et al., "Submicron-Sized Spherical Yttrium Oxide Based Phosphors Prepared by Supercritical CO2-Assisted aerosolization and pyrolysis," Appl. Phys. Lett., Vol. 71, No.12, September 22, 1997, pp. 1643-1645. BS Courtecuisse, V.G. et al., "Kinetics of the Titanium Isopropoxide Decomposition in Supercritical Isopropyl Alcohol, " Ind. Eng. Chem. Res., Vol. 35, No. 8, pp. 2539-2545, Aug 1996. BT Gallagher-Wetmore, P. et al., "Supercritical Fluid Processing: A New Dry Technique for Photoresist Developing," SPIE Vol. 2438, pp.694-708, Jun. 1995. BU ΒV Purtell, R, et al., "Precision Parts Cleaning using Supercritical Fluids, "J. Vac, Sci, Technol. A. Vol. 11, No. 4, July 1993, pp. 1696-1701. Matson, D.W. et al., "Rapid Expansion of Supercritical Fluid Solutions: Solute Formation of Powders, Thin Films, and Fibers," Ind. Eng. Chem. Res., Vol. 26, No. 11, pp. 2298-2306, 1987. RW Tolley, W.K. et al., "Stripping Organics from Metal and Mineral Surfaces using Supercritical Fluids," Separation Science and Technology, Vol. 22, pp. 1087-1101, 1987. BXJoseph L. Foszcz, "Diaphragm Pumps Eliminate Seal Problems", Plant Engineering, pp. 1-5, February 1, 1996. BY ΒZ Bob Agnew, "WILDEN Air-Operated Diaphragm Pumps", Process & Industrial Training Technologies, Inc., 1996. CA CB CC CD CE CF CG CH CI CJ CK CL CM Date Considered: Examiner: **EXAMINER:** Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Page 1 of 2 Fee transmittal

FEE TRANSMITTAL

Electronic Version v08 Stylesheet Version v08.0

Title of Invention

HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE

Application Number:

09/912844

09/912844

Date:

2001-07-24

TOTAL FEE AUTHORIZED \$180

First Named Applicant: Maximilian A. Biberger Attorney Docket Number:

Patent fees are subject to annual revisions on or about October 1st of each year.

BASIC FILING FEE

Fee Description	Fee Code	Amount \$	Fee Paid \$
Submission Of Information Disclosure Stmt Fee	1806	180	180

AUTHORIZED BILLING INFORMATION

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10/29/2003

Fee transmittal

Page 2 of 2

Access Code

Deposit name:

Haverstock and Owens LLP

Deposit authorized name: Thomas B. Haverstock

Signature:

/tbh/

Date (YYYYMMDD):

2003-10-29

Charge Any Additional Fee Required Under 37 C.F.R. Sections 1.16 and 1.17.

Page 1 of 2 Acknowledgement Receipt

UNITED STATES PATENT AND TRADEMARK OFFICE ACKNOWLEDGEMENT RECEIPT

Electronic Version 1.1 Stylesheet Version v1.1.1

Title of Invention	HIGH PRESSURE	PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE
Submission Type:	Information [Disclosure Statement
Application Number:	09/912844	*09/912844*
EFS ID:	49914	
Server Response:	Confirmation Code	Message
	ISVR1	Submission was successfully submitted – Even if Informational or Warning Messages appear below, please do not resubmit this application
	ICON1	5915
	ISYS5	Filename= N/A BusinessRule= Validation System/Function Call Information. #Supporting Msg:Server unable to validate the Confirmaton/Application numbers at this time. They will be checked by PTO personnel later.
First Named Applicant: Maximilian Biberger		
Attorney Docket Numbe	r:	
Timestamp:	2003-10-29	12:27:57 EDT
From:	us	
File Listing:		

 $file: //G: \\ \label{file: filed} IDS-E-Filed \\ \label{file: filed} SSI00501 \\ \label{file: filed} SSI00501 \\ \label{file: filed} A \\ \label{file: filed} SSI00501 \\ \label{file: filed} A \\ \label{file: filed} SSI00501 \\ \label{file: filed} A \\ \label{file: filed} SSI00501 \\ \label{filed: filed} A \\ \label{filed: filed: fi$

10/29/2003

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Page 2 of 2

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Digital Certificate Holder Name:	cn=Thomas B. Haverstock, ou=Registered Attorneys, ou=Patent and Trademark Office, ou=Department of Commerce, o=U.S. Government, c=US				

Page 1 of 2

TRANSMITTAL

Stylesheet Version v1.1.0 Electronic Version v1.1

Application Number: Invention Title of HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE 09/912844 *09/912844*

2001-07-24

First Named Applicant: Maximilian A. Biberger

Attorney Docket Number: Confirmation Number: 5915

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Submitted by:	Elec. Sign.	Sign. Capacity
Thomas B. Haverstock	/tbh/	
Registered Number: 32571		Attorney

Documents being submitted	Files
us-fee-sheet	SSI00501A-usfees.xml
	us-fee-sheet.xsl
	us-fee-sheet.dtd
us-ids	SSI00501A-usidst.xml
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	us-ids.xsl
Comments	

09/912844

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18 Stylesheet Version v18.0

> HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR Title of SUBSTRATE Invention

Application Number: 09/912844

Confirmation Number: 5915

First Named Applicant: Maximilian Biberger

Attorney Docket Number:

Search string: (2617719 or 2625886 or 3744660 or 3968885 or 4029517 or

4091643 or 4245154 or 4341592 or 4355937 or 4367140 or 4406596 or 4422651 or 4474199 or 4522788 or 4549467 or 4592306 or 4601181 or 4626509 or 4670126 or 4682937 or 4693777 or 4749440 or 4778356 or 4789077 or 4823976 or 4825808 or 4827867 or 4838476 or 4865061 or 4879431 or 4917556 or 4924892 or 4951601 or 4960140 or 4983223 or 5011542 or 5044871 or 5062770 or 5071485 or 5105556 or 5167716 or 5169296 or 5169408 or 5186718 or 5188515 or

\$190373 or \$191993).pn.

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class
	1	2617719	1952-11-11	C. R. Stewart		
	2	2625886	1953-01-20	Browne	٦	
	3	3744660	1973-07-10	Gaines et al.	7	
	4	3968885	1976-07-13	Hassan et al.	٦	
	5	4029517	1977-06 14	Rand	٦	
	6	4091643	1978-05-30	Zucchini	Ï	
	7	4245154	1981-01-13	Uehara et al.	٦	
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1 1	8	4341592	1982-07-27	Shortes et al.
	9	4355937	1982-10-26	Mack et al.
	10	4367140	1983-01-04	Wilson
	11	4406596	1983-09-27	Budde
	12	4422651	1983-12-27	Platts
	13	4474199	1984-10-02	Blaudszun
	14	4522788	1995-06-11	Sitek et al.
	15	4549467	1985-10-29	Wilden et al.
	16	4592306	1986-06-03	Gallego
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	18	4626509	1986-12-02	Lyman
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	20	4682937	1987-07-28	Credle, Jr.
	21	4693777	1987-09-15	Hazano et al.
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	25	4823976	1989-04-25	White, lil et al.
	26	4825808	1989-05-02	Takahashi et al.
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Information Disclosure Statement

Page 3 of 3

40	5105556	1992-04-21	Kurokawa et al.
41	5167716	1992-12 01	Boitnott et al.
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43	5169408	1992-12-08	Biggerstaff et al.
44	5186718	1993-02-16	Tepman et al.
45	5188515	1993-02-23	Horn
46	5190373	1993-03-02	Dickson et al.
47	5191993	1993 -03-09	Wanger et al.

Remarks

Note: Remarks are not for responding to an office action.

Non US Patent and Publication references shall be filed under a separate paper transmittal. The current electronic filing contains part 1 out of a total of 4 electronic filings.

Signature

ı	Examiner Name	Date
ı		

UNITED STATES PATENT AND TRADEMARK OFFICE ACKNOWLEDGEMENT RECEIPT

Electronic Version 1.1 Stylesheet Version v1.1.1

Title of Invention	HIGH PRESSURE	E PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE
Submission Type:	Information (Disclosure Statement
Application Number:	09/912844	*09/912844
EFS ID:	49915	
Server Response:	Confirmation Code	Message
	ISVR1	Submission was successfully submitted - Even if Informational or Warning Messages appear below please do not resubmit this application
	ICON1	5915
	ISYS5	Filename = N/A BusinessRule = Validation System/Function Call Information. #Supporting Msg:Server unable to validate the Confirmaton/Application numbers at this time. They will be checked by PTO personnel later.
First Named Applicant:	iberger	
Attorney Docket Number	r:	
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Page 2 of 2

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Page 2 of 2

TRANSMITTAL

Electronic Version v1.1

Stylesheet Version v1.1.0

Title of HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE Invention

Application Number: 09/912844 *09/912844*

2001-07-24

First Named Applicant: Maximilian A. Biberger

Confirmation Number: 5915

Attorney Docket Number:

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homas B. Haverstock	/tbh/	
legistered Number: 32571		Attorney

Documents being submitted	Files
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Comments	

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18 Stylesheet Version v18.0

> HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR Title of SUBSTRATE Invention

Application Number: Confirmation Number:

09/912844 09/912844

First Named Applicant: Maximilian Biberger

Search string:

Attorney Docket Number:

(\$193\$60 or \$195878 or \$213485 or \$221019 or \$222876 or 5224504 or 5236669 or 5240390 or 5243821 or 5246500 or 5251776 or 5280693 or 5285352 or 5288333 or 5339844 or 5370741 or 5412958 or 5433334 or 5447294 or 5503176 or 5505219 or 5509431 or 5571330 or 5589224 or 5621982 or

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US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

lſ	init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
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H		2	5195878	1993-03-23	Sahiavo et al.]		
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П		4	5221019	1993-06-22	Pechacek]		
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Н		6	5224504	1993-07-06	Thompson et al.]		
Н		7	5236669	1993-08-17	Simmons et al.]		
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П		10	5246500	1993-09-21	Samata et al.]		

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Information Disclosure Statement

Page 3 of 3

Examiner Name	Date	

$\overline{\Box}$	11	5251776	1993-10-12	Morgan Jr. et al.	
\Box	12	5280693	1994-01-25	Heudecker	
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Remarks

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UNITED STATES PATENT AND TRADEMARK OFFICE ACKNOWLEDGEMENT RECEIPT

Electronic Version 1.1 Stylesheet Version v1.1.1

Title of Invention	HIGH PRESSURE	PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE
Submission Type:	Information [Disclosure Statement
Application Number:	09/912844	*09/912844*
EFS ID:	49916	
Server Response:	Confirmation Code	Message
	ISVR1	Submission was successfully submitted – Even if Informational or Warning Messages appear below, please do not resubmit this application
	ICON1	5915
	ISYS5	Filename= N/A BusinessRule= Validation System/Function Call Information. #Supporting Msg:Server unable to validate the Confirmaton/Application numbers at this time. They will be checked by PTO personnel later.
First Named Applicant:	Maximilian Bi	berger
Attorney Docket Number:		
Timestamp:	2003-10-29	12:38:41 EDT
From:	us	
File Listing:		

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Page 2 of 2

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HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE Invention Title of

09/912844 09/912844 Application Number:

Maximilian A. Biberger 2001-07-24 First Named Applicant:

Confirmation Number: 5915

Attorney Docket Number:

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Submitted by:	Elec. Sign.	Sign. Capacity
Thomas B. Haverstock	'tbh/	
Registered Number: 32571		Attorney

Documents being submitted	Files
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Page 2 of 2

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09/912844

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18 Stylesheet Version v18.0

> HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR Title of SUBSTRATE Invention

Application Number: 09/912844

Confirmation Number: 5915

Maximillan Biberger

First Named Applicant: Attorney Docket Number:

Search string:

(5900107 or 5904737 or 5932100 or 5934991 or 5981399 or 5989342 or 6005226 or 6017820 or 6029371 or 6037277 or 6053348 or 6056008 or 6077053 or 6082150 or 6085935 or 6097015 or 6128830 or 6145519 or 6159295 or 6164297 or 6203582 or 6216364 or 6239038 or 6241825 or 6251250 or 6277753 or 6286231 or 6305677 or 6334266 or 6344174 or 6388317 or 6389677 or 6418956 or 6436824 or 6454945 or 6464790).pn.

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Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patent ee	Kind	Class	Subclass
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	2	5904737	1999-05-18	Preston et al.]		
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Remarks

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Title of Invention	HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE				
Submission Type:	Information D	Disclosure Statement			
Application Number:	09/912844 *09/912844				
EFS ID:	4991 7				
Server Response:	Confirmation Code	Message			
	ISVR1	Submission was successfully submitted – Even if Informational or Warning Messages appear below please do not resubmit this application			
	ICON1	5915			
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First Named Applicant: Thomas Haverstock		rstock			
Attorney Docket Number					
Timestamp:	2003-10-29	2003-10-29 12:43:21 EDT			
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Page 2 of 2

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HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE Invention Title of

09/912844 09/912844 Application Number:

2001-07-24

Thomas 8. Haverstock First Named Applicant:

Confirmation Number: 5915

Attorney Docket Number:

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Submitted by:	Elec. Sign.	Sign. Capacity
Maximilian A. Biberger	/tbh/	
Registered Number: 32571		Attorney

Documents being submitted	Files
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	us-ids.xsl
Comments	

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v1 8 Stylesheet Version v18.0

Title of

Invention

HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR

SUBSTRATE

Application Number: 09/912844 Confirmation Number: 5915

09/912844

First Named Applicant: Thomas Haverstock

Attorney Docket Number:

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5217043 or 20020001929).pn.

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Note: Applicant is not required to submit a paper copy of cited US Patent Documents

1	init	Clte.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
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		2	6541278	2003-04-01	Morita et al.	BI		
		3	6546946	2003-04-15	Dunmire	81		
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init	Cite.No.	Pub. No.	Date	Applicant	Kind	Class	Subclass
	1	20020001929	2002-01-03	Biberger et al.	Al		

Remarks

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